

# SEMiX151GAR12E4s



SEMiX<sup>®</sup> 1s

## Trench IGBT Modules

### SEMiX151GAR12E4s

#### Features

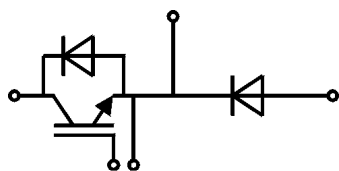
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

#### Typical Applications\*

- AC inverter drives
- UPS
- Electronic Welding

#### Remarks

- Case temperature limited to  $T_C=125^\circ\text{C}$  max.
- Product reliability results are valid for  $T_j=150^\circ\text{C}$



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#### Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	232	A
		$T_c = 80^\circ\text{C}$	179	A
$I_{Cnom}$		150	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	450	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 20\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Inverse diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	189	A
		$T_c = 80^\circ\text{C}$	141	A
$I_{Fnom}$		150	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	450	A	
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	900	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Freewheeling diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	189	A
		$T_c = 80^\circ\text{C}$	141	A
$I_{Fnom}$		150	A	
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$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	600	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

#### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.8	2.05	V
		$T_j = 150^\circ\text{C}$	2.2	2.4	V
$V_{CE0}$	chipelevel	$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	6.7	7.7	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	10.0	10.7	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 6\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$		2.0	$\text{mA}$
		$T_j = 150^\circ\text{C}$			$\text{mA}$
$C_{ies}$	$V_{CE} = 25\text{ V}$		9.3		$\text{nF}$
$C_{oes}$	$V_{GE} = 0\text{ V}$		0.58		$\text{nF}$
$C_{res}$			0.51		$\text{nF}$
$Q_G$	$V_{GE} = -8\text{ V...} + 15\text{ V}$		850		$\text{nC}$
$R_{Gint}$	$T_j = 25^\circ\text{C}$		5.00		$\Omega$

# SEMiX151GAR12E4s



SEMiX® 1s

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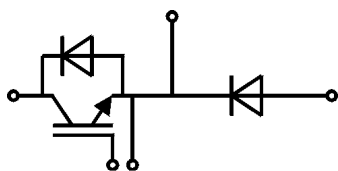
#### Typical Applications\*

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- UPS
- Electronic Welding

#### Remarks

- Case temperature limited to  $T_C=125^\circ\text{C}$  max.
- Product reliability results are valid for  $T_j=150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		204		ns
$t_r$	$I_C = 150\text{ A}$	$T_j = 150^\circ\text{C}$		42		ns
$E_{on}$	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		16.6		mJ
$t_{d(off)}$	$R_{G\ on} = 1\ \Omega$	$T_j = 150^\circ\text{C}$		468		ns
$t_f$	$R_{G\ off} = 1\ \Omega$	$T_j = 150^\circ\text{C}$		91		ns
$E_{off}$	$di/dt_{on} = 3900\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		18.4		mJ
	$di/dt_{off} = 2000\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per IGBT				0.19	K/W
Inverse diode						
$V_F = V_{EC}$	$I_F = 150\text{ A}$	$T_j = 25^\circ\text{C}$		2.1	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.1	2.4	V
	chipllevel					
$V_{F0}$		$T_j = 25^\circ\text{C}$	1.1	1.3	1.5	V
	chipllevel	$T_j = 150^\circ\text{C}$	0.7	0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$	4.3	5.6	6.4	m $\Omega$
	chipllevel	$T_j = 150^\circ\text{C}$	6.7	7.8	8.5	m $\Omega$
$I_{RRM}$	$I_F = 150\text{ A}$	$T_j = 150^\circ\text{C}$		115		A
$Q_{rr}$	$di/dt_{off} = 3400\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		23		$\mu\text{C}$
$E_{rr}$	$V_{GE} = -15\text{ V}$	$T_j = 150^\circ\text{C}$		8.9		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per diode				0.31	K/W
Freewheeling diode						
$V_F = V_{EC}$	$I_F = 150\text{ A}$	$T_j = 25^\circ\text{C}$		2.1	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.1	2.4	V
	chipllevel					
$V_{F0}$		$T_j = 25^\circ\text{C}$	1.1	1.3	1.5	V
	chipllevel	$T_j = 150^\circ\text{C}$	0.7	0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$	4.3	5.6	6.4	m $\Omega$
	chipllevel	$T_j = 150^\circ\text{C}$	6.7	7.8	8.5	m $\Omega$
$I_{RRM}$	$I_F = 150\text{ A}$	$T_j = 150^\circ\text{C}$		115		A
$Q_{rr}$	$di/dt_{off} = 3400\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		23		$\mu\text{C}$
$E_{rr}$	$V_{GE} = -15\text{ V}$	$T_j = 150^\circ\text{C}$		8.9		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per diode				0.31	K/W
Module						
$L_{CE}$				16		nH
$R_{CC+EE}$	res., terminal-chip	$T_C = 25^\circ\text{C}$		0.7		m $\Omega$
		$T_C = 125^\circ\text{C}$		1		m $\Omega$
$R_{th(c-s)}$	per module			0.075		K/W
$M_s$	to heat sink (M5)		3		5	Nm
$M_t$		to terminals (M6)	2.5		5	Nm
						Nm
$w$					145	g
Temperature Sensor						
$R_{100}$	$T_C=100^\circ\text{C}$ ( $R_{25}=5\text{ k}\Omega$ )			$493 \pm 5\%$		$\Omega$
$B_{100/125}$	$R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$ ; $T[K]$ ;			$3550 \pm 2\%$		K



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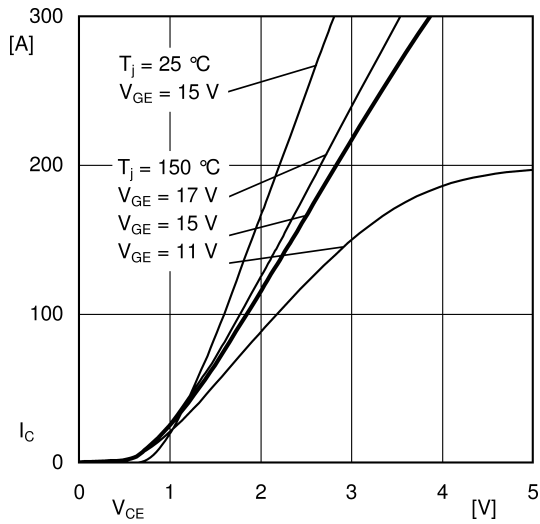


Fig. 1: Typ. output characteristic, inclusive  $R_{CC+EE}$

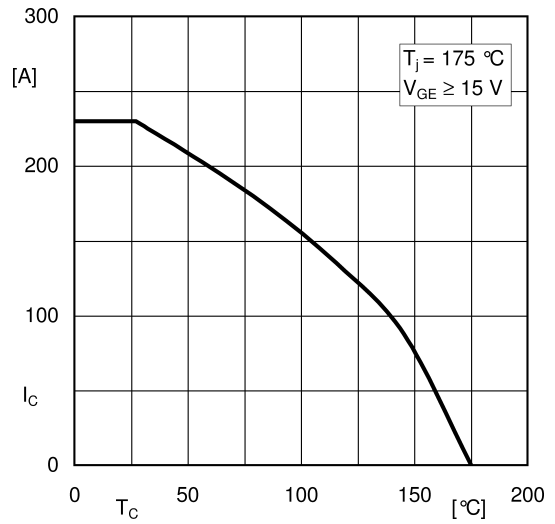


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

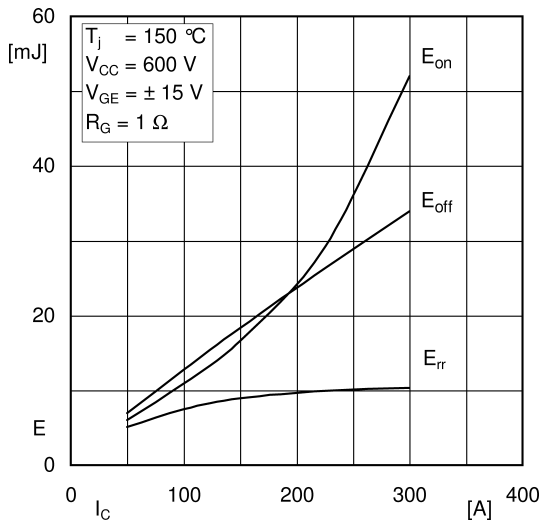


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

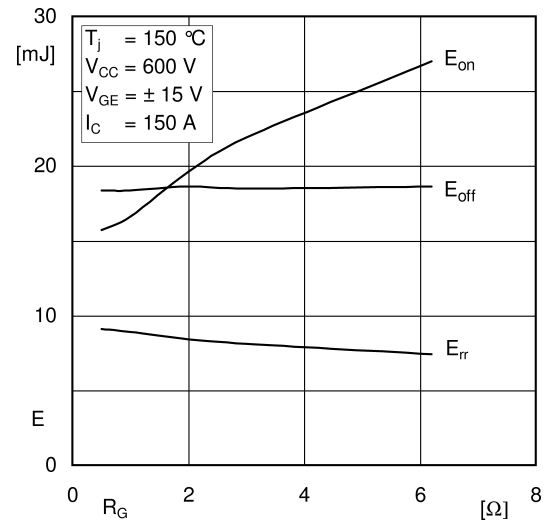


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

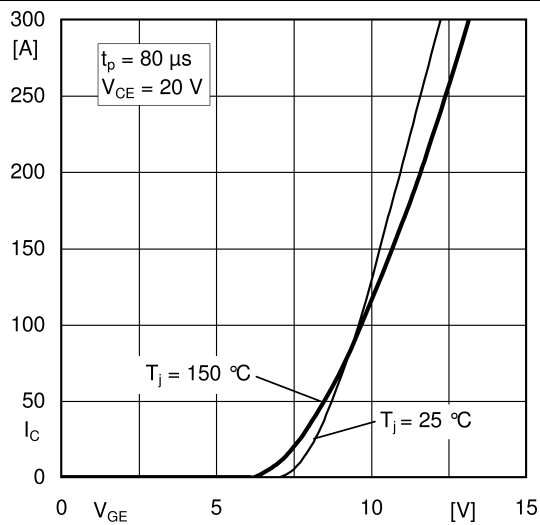


Fig. 5: Typ. transfer characteristic

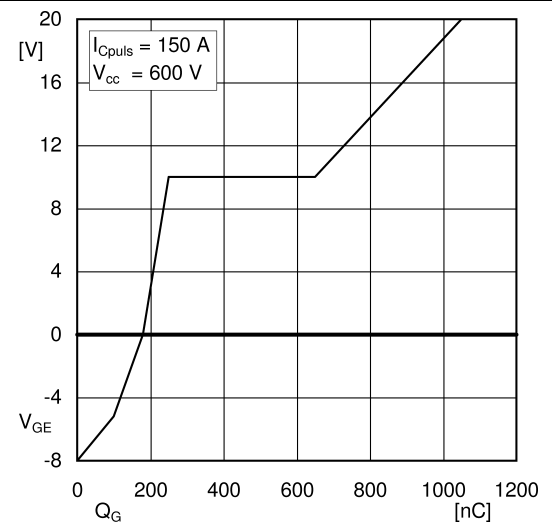


Fig. 6: Typ. gate charge characteristic

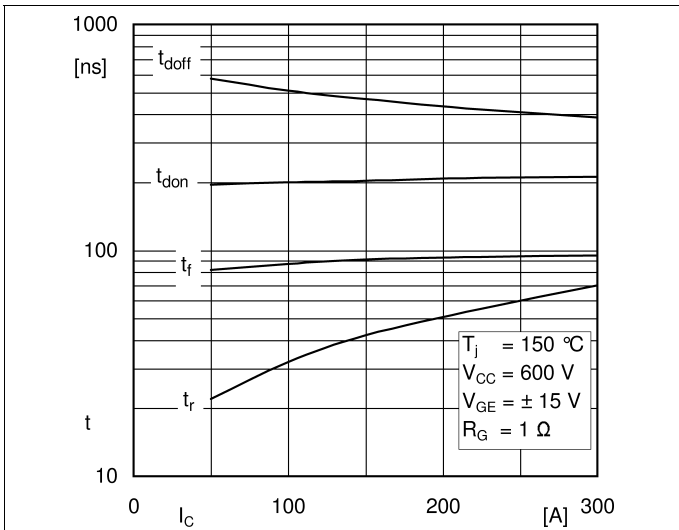


Fig. 7: Typ. switching times vs.  $I_C$

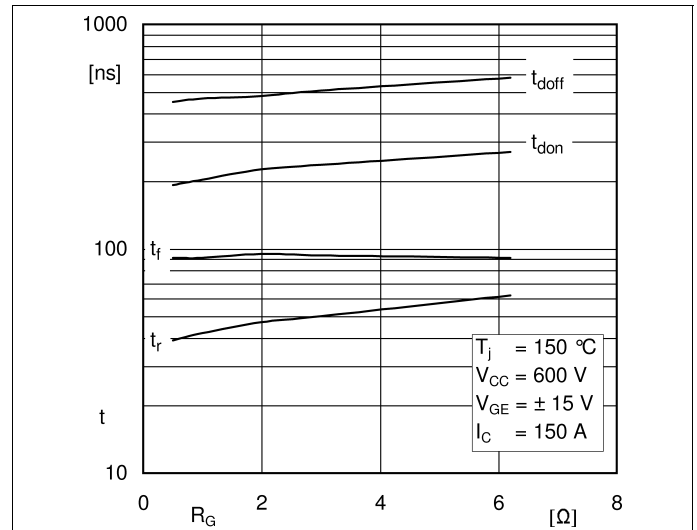


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

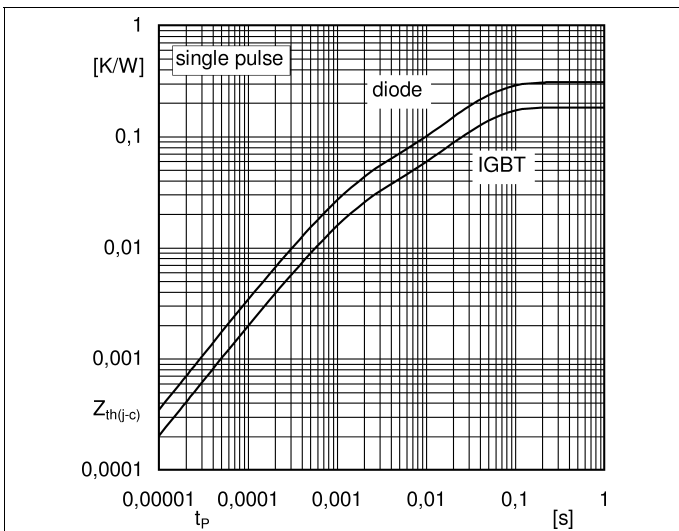


Fig. 9: Typ. transient thermal impedance

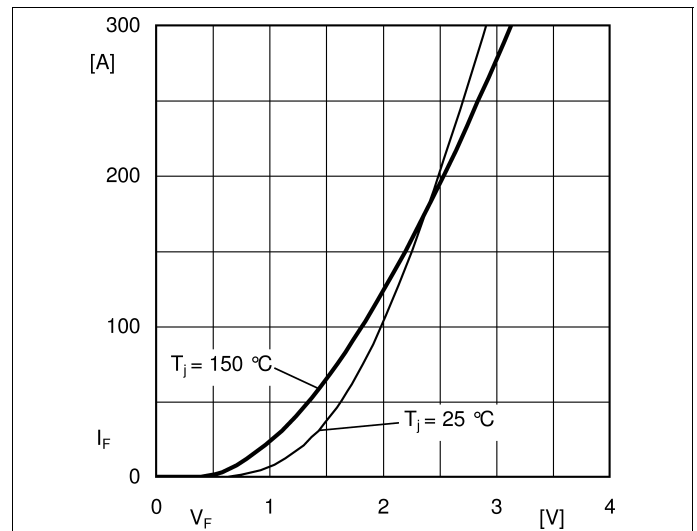


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC+EE'}$

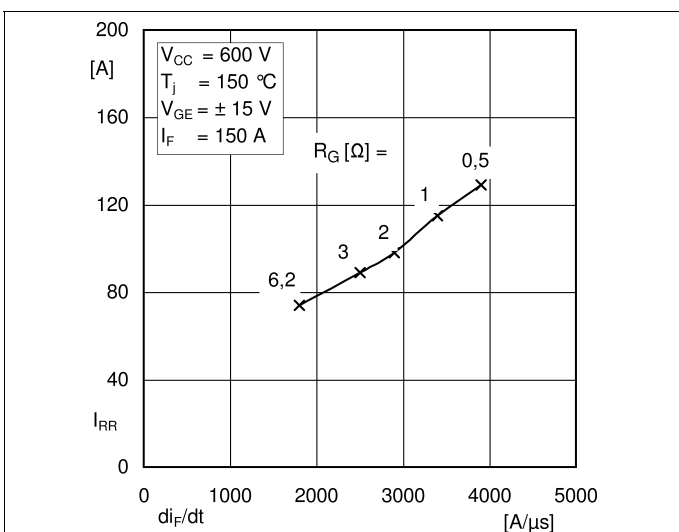


Fig. 11: Typ. CAL diode peak reverse recovery current

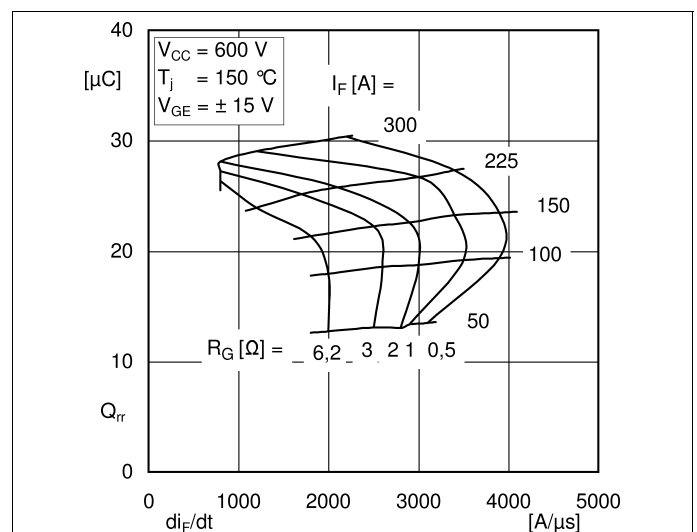
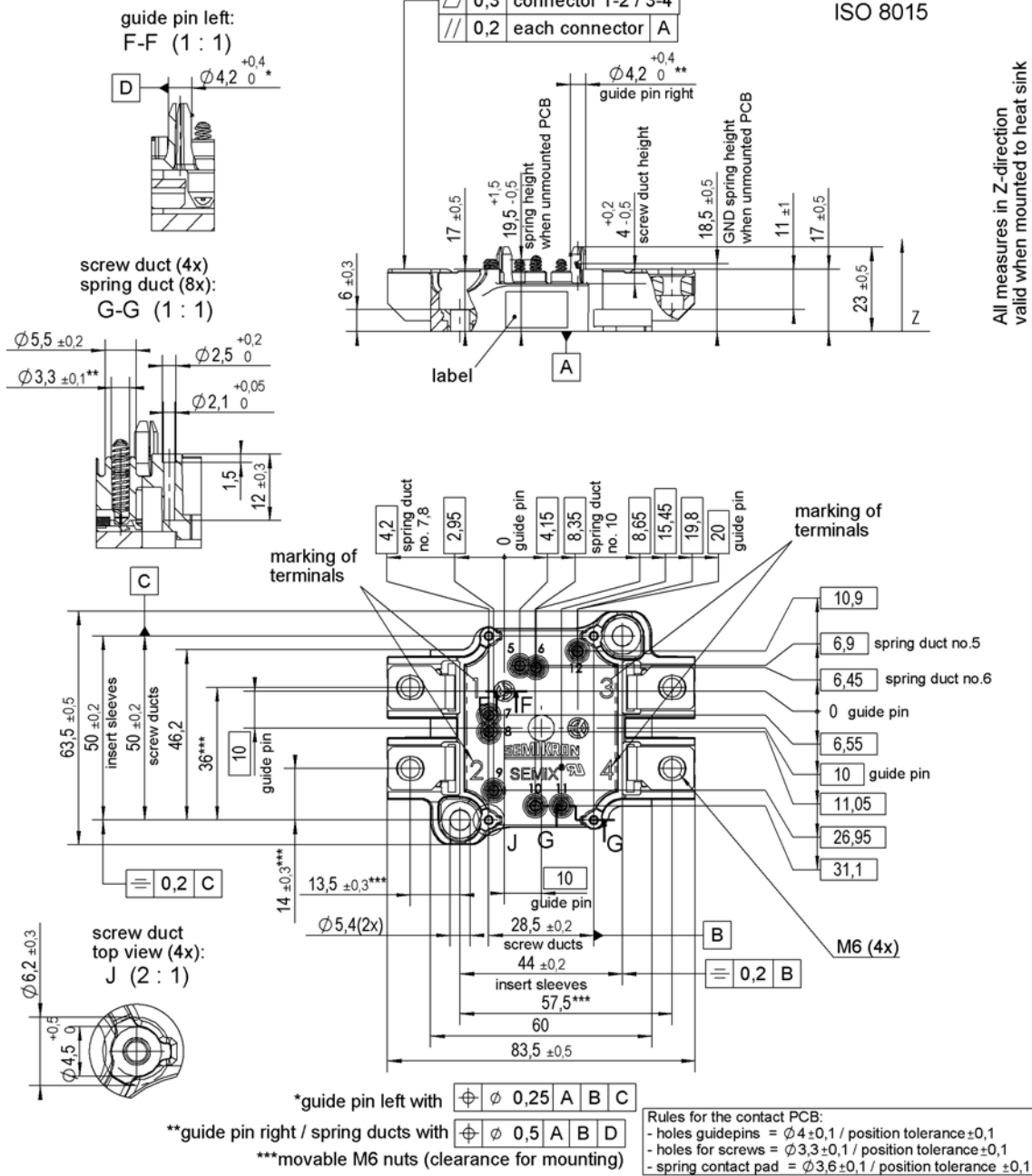


Fig. 12: Typ. CAL diode recovery charge

# SEMiX151GAR12E4s

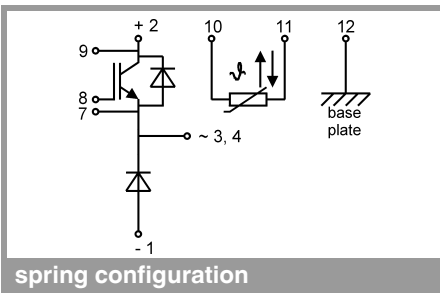
Case: SEMiX 1s

general tolerance:  
ISO 2768-m  
ISO 8015



All measures in Z-direction  
valid when mounted to heat sink

SEMIX 1s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.